

SUBSTRATE PROCESSING METHOD AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A method including providing a substrate in a process chamber of a substrate processing apparatus, the substrate having a first region containing a silicon oxide film and a second region containing a film other than the silicon oxide film; adsorbing hydrogen fluoride on the substrate; and exposing the substrate with the absorbed hydrogen fluoride to plasma generated from an inert gas to selectively etch the first region with respect to the second region.

(FIG. 2A)